



#8

SHEET 1 OF 1

Form PTO 1449
(Modified)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY DOCKET NO.
210313US2SRDSERIAL NO.
09/891,129

LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Akira NISHIYAMA, et al.

FILING DATE

June 26, 2001

GROUP

2814

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
	AO					
	AP					
	AQ					
	AR					
	AS					
	AT					
	AU					
	AV					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

A-M	AW	M.R. Visokay, et al. Application of HfSiON as a gate dielectric material, Applied Physics Letters, Volume 80, Number 17, 29 April 2002, Pages 3183-3185
	AX	
	AY	
	AZ	

☐ Additional References sheet(s) attached

Examiner

ANH D. MAI

Date Considered

11/09/03

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.